

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,115,344 B2
APPLICATION NO. : 10/777060
DATED : October 3, 2006
INVENTOR(S) : N. Hasegawa et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Claims

Please amend claims 1 and 8 as follows:

1. A method of manufacturing a semiconductor device, comprising the steps of:
preparing a phase shifting mask including (a) an element forming area having a semitransparent phase shifting film, and (b) a light shielding area provided at a peripheral edge of said element forming area and serving to make an intensity of light having passed through said light shielding area smaller than an intensity of light having passed through said semitransparent phase shifting film, as measured on a to-be-exposed photoresist film, and said light shielding area further including a target pattern for mask aligning; and
transmitting, with a projection exposure optical system, a pattern formed on said element forming area of said phase shifting mask onto said photoresist film.
8. A method of manufacturing a semiconductor device, comprising the steps of:
preparing a phase shifting mask including (a) an element forming area having a first semitransparent phase shifting film having a transmittance with respect to exposure light not higher than 25%, and (b) a light shielding area provided at a peripheral edge of said element forming area and serving to make an intensity of light having passed through said light shielding area smaller than an intensity of light having passed through said semitransparent phase shifting film, as measured on a to-be-exposed photoresist film, and said light shielding area further including a target pattern for mask aligning;

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,115,344 B2
APPLICATION NO. : 10/777060
DATED : October 3, 2006
INVENTOR(S) : N. Hasegawa et al.

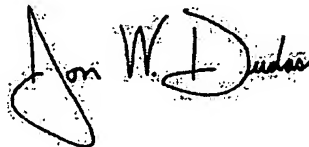
Page 2 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

preparing a semiconductor substrate at which said photoresist film to be exposed is formed; and transmitting, with a projection exposure optical system, a pattern formed on said element forming area of said phase shifting mask onto said photoresist film.

Signed and Sealed this

Ninth Day of January, 2007

A handwritten signature in black ink, appearing to read "Jon W. Dudas", with a stylized flourish at the end.

JON W. DUDAS
Director of the United States Patent and Trademark Office